

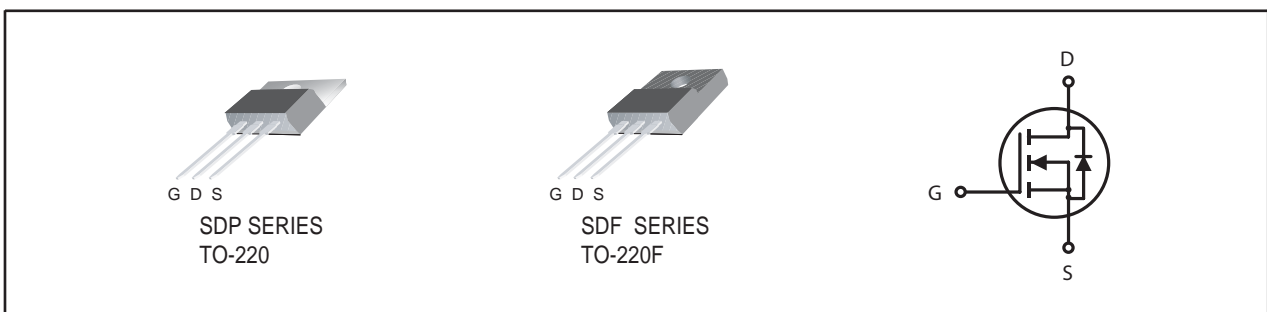


N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DS}	I _D	R _{DS(ON)} (Ω) Typ
800V	7A	1.4 @ V _{GS} =10V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO-220 and TO-220F Package.



ORDERING INFORMATION

Ordering Code	Package	Marking Code	Delivery Mode	RoHS Status
SDP07N80HZ	TO-220	SDP07N80	Tube	Halogen Free
SDP07N80PZ	TO-220	07N80	Tube	Pb Free
SDF07N80HZ	TO-220F	SDF07N80	Tube	Halogen Free
SDF07N80PZ	TO-220F	07N80	Tube	Pb Free

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter	SDP07N80	SDF07N80	Units	
V _{DS}	Drain-Source Voltage	800		V	
V _{GS}	Gate-Source Voltage	±30	±30	V	
I _D	Drain Current-Continuous ^a	T _C =25°C	7	7	A
		T _C =100°C	4.2	4.2	A
I _{DM}	-Pulsed ^a	28	28	A	
E _{AS}	Single Pulse Avalanche Energy ^c	650		mJ	
P _D	Maximum Power Dissipation	T _C =25°C	167	56	W
		T _C =100°C	67	22	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150		°C	

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case	0.75	2.25	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

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ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

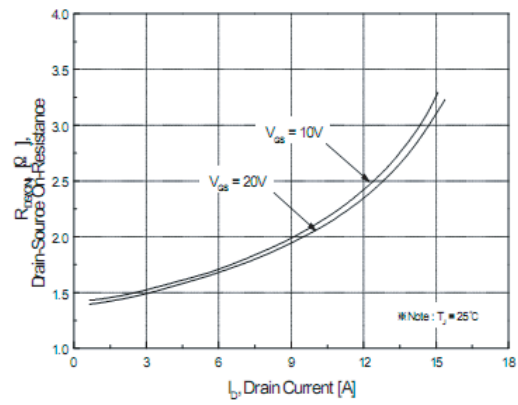
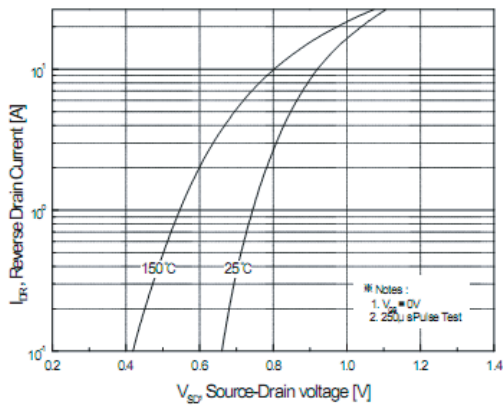
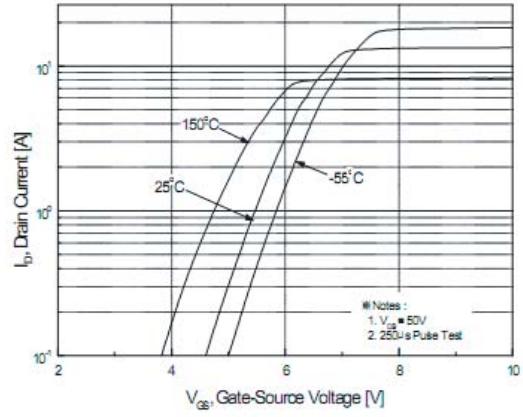
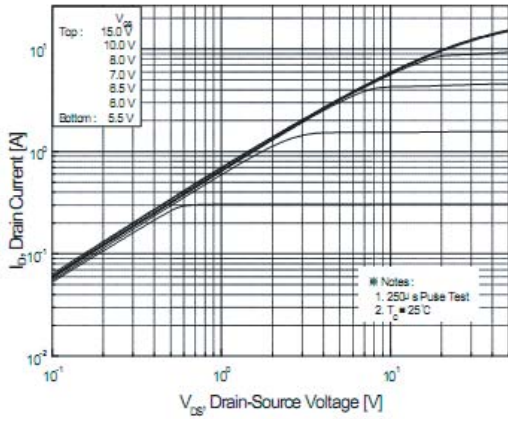
Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	800			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =640V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	3		5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =3.5A		1.4	1.9	ohm
DYNAMIC CHARACTERISTICS^b						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		1300		pF
C _{OSS}	Output Capacitance			120		pF
C _{RSS}	Reverse Transfer Capacitance			10		pF
SWITCHING CHARACTERISTICS^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =400V I _D =1.0A R _{GEN} = 25 ohm		40		ns
t _r	Rise Time			100		ns
t _{D(OFF)}	Turn-Off Delay Time			50		ns
t _f	Fall Time			60		ns
Q _g	Total Gate Charge	V _{DS} =640V, I _D =1.0A, V _{GS} =10V		27		nC
Q _{gs}	Gate-Source Charge	V _{DS} =640V, I _D =1.0A, V _{GS} =10V		8		nC
Q _{gd}	Gate-Drain Charge			11		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =7.0A			1.4	V
Notes						
<p>a. Drain current limited by maximum junction temperature.</p> <p>b. Guaranteed by design, not subject to production testing.</p> <p>c. Starting T_J=25°C, L=25mH, V_{DD} = 50V.</p>						

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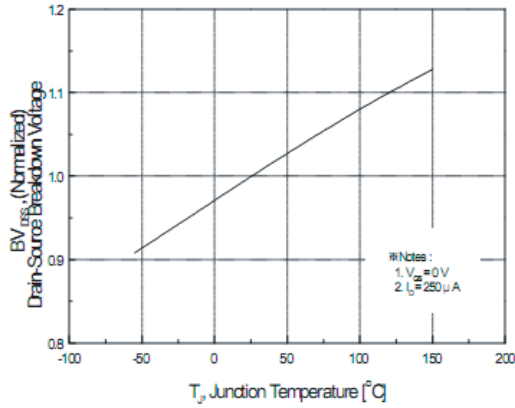


Figure 7. Breakdown Voltage Variation vs Temperature

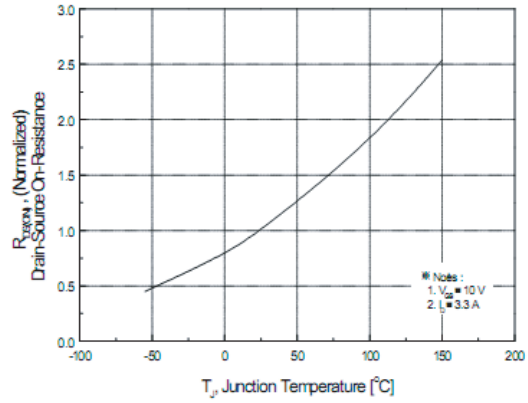


Figure 8. On-Resistance Variation vs Temperature

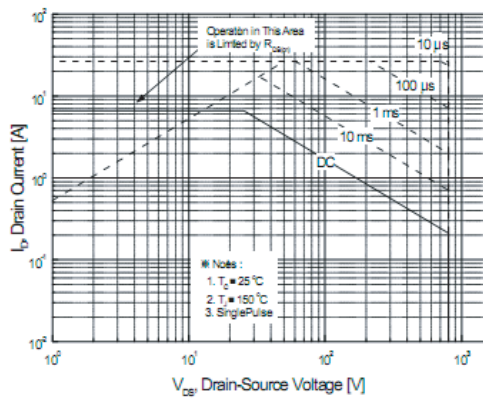


Figure 9-1. Maximum Safe Operating Area for TO220

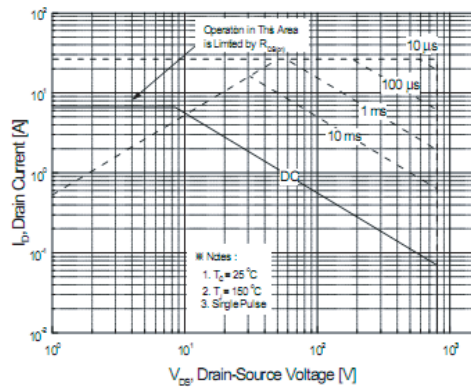


Figure 9-2. Maximum Safe Operating Area for TO220F

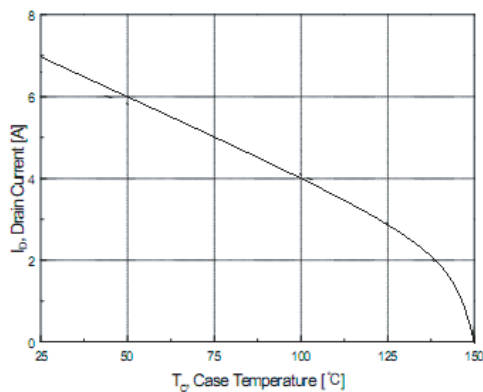


Figure 10. Maximum Drain Current vs Case Temperature

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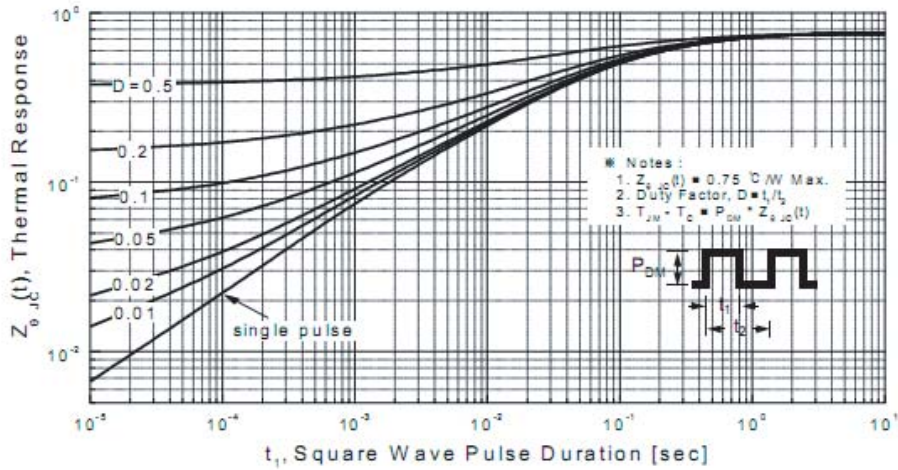


Figure 11-1. Transient Thermal Response Curve for TO220

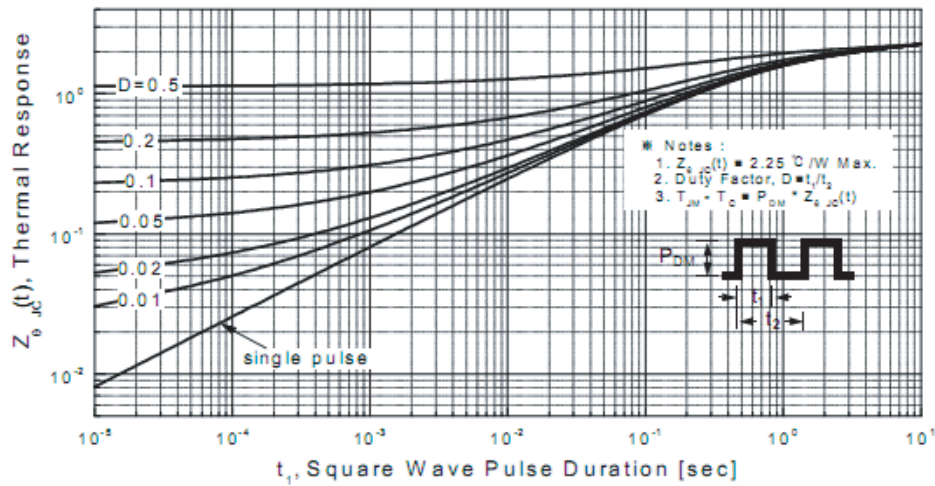


Figure 11-2. Transient Thermal Response Curve for TO220F

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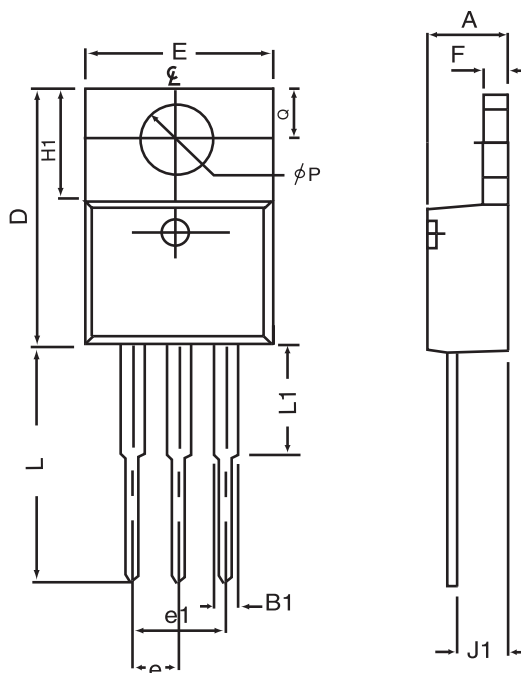
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PACKAGE OUTLINE DIMENSIONS

TO-220



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.32	4.80	0.170	0.189
B1	1.27	1.65	0.050	0.630
D	14.6	16.00	0.575	0.610
E	9.70	10.41	0.382	0.410
e	2.34	2.74	0.092	0.108
e1	4.68	5.48	0.184	0.216
F	1.14	1.40	0.045	0.055
H1	5.97	6.73	0.235	0.265
J1	2.20	2.79	0.087	0.110
L	12.88	14.22	0.507	0.560
L1	3.00	6.35	0.120	0.250
ϕP	3.50	3.94	0.138	0.155
Q	2.54	3.05	0.100	0.120

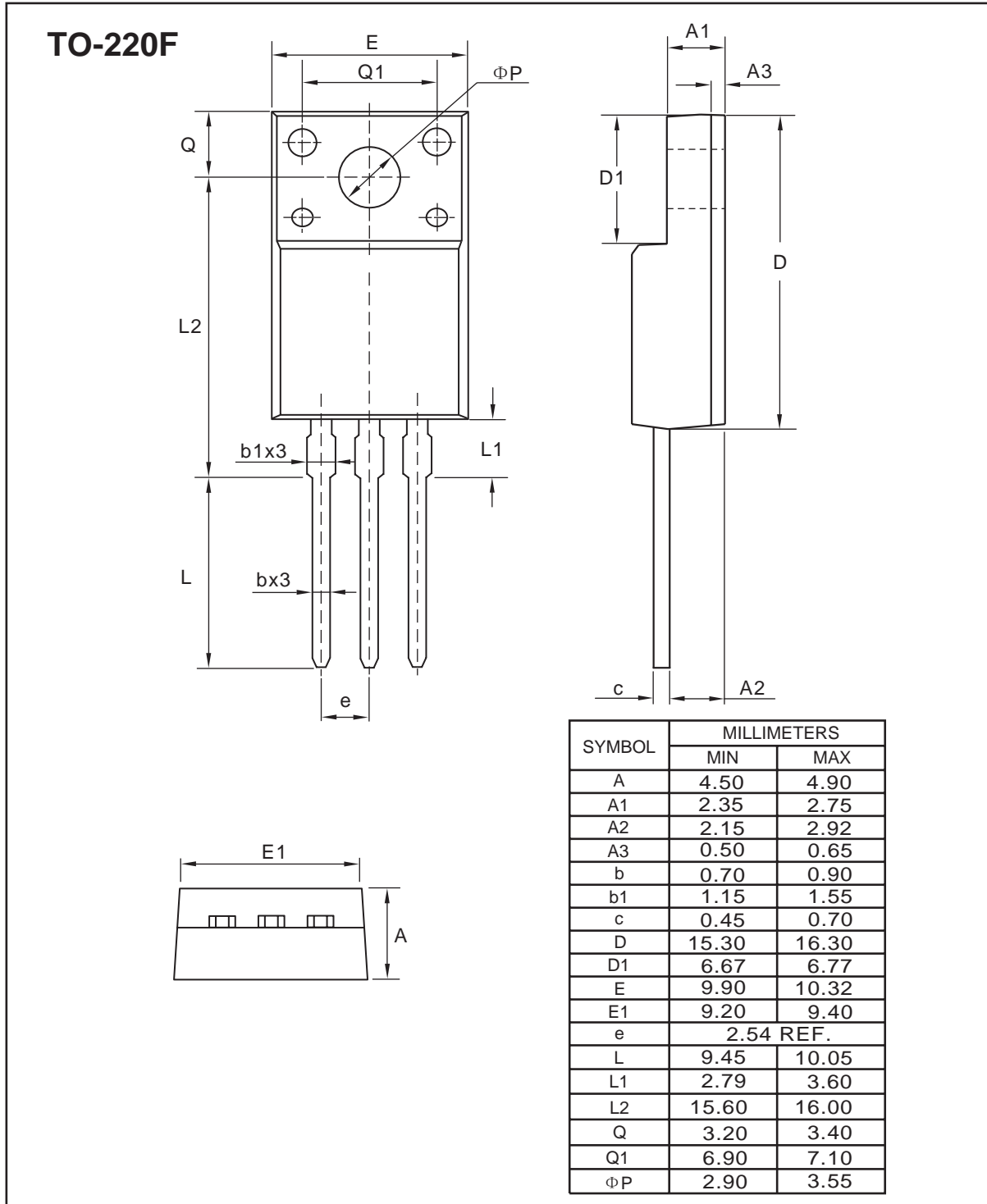
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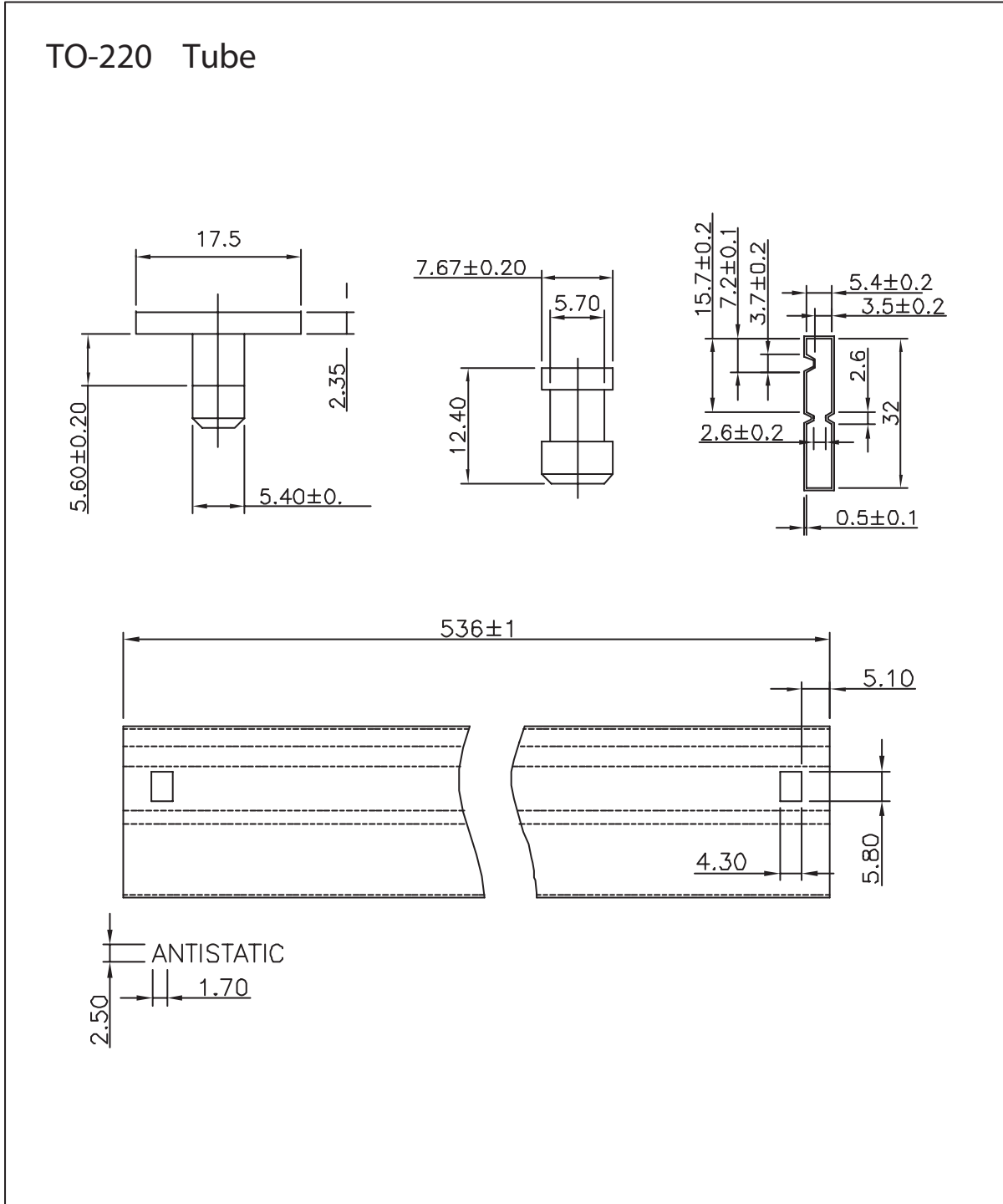


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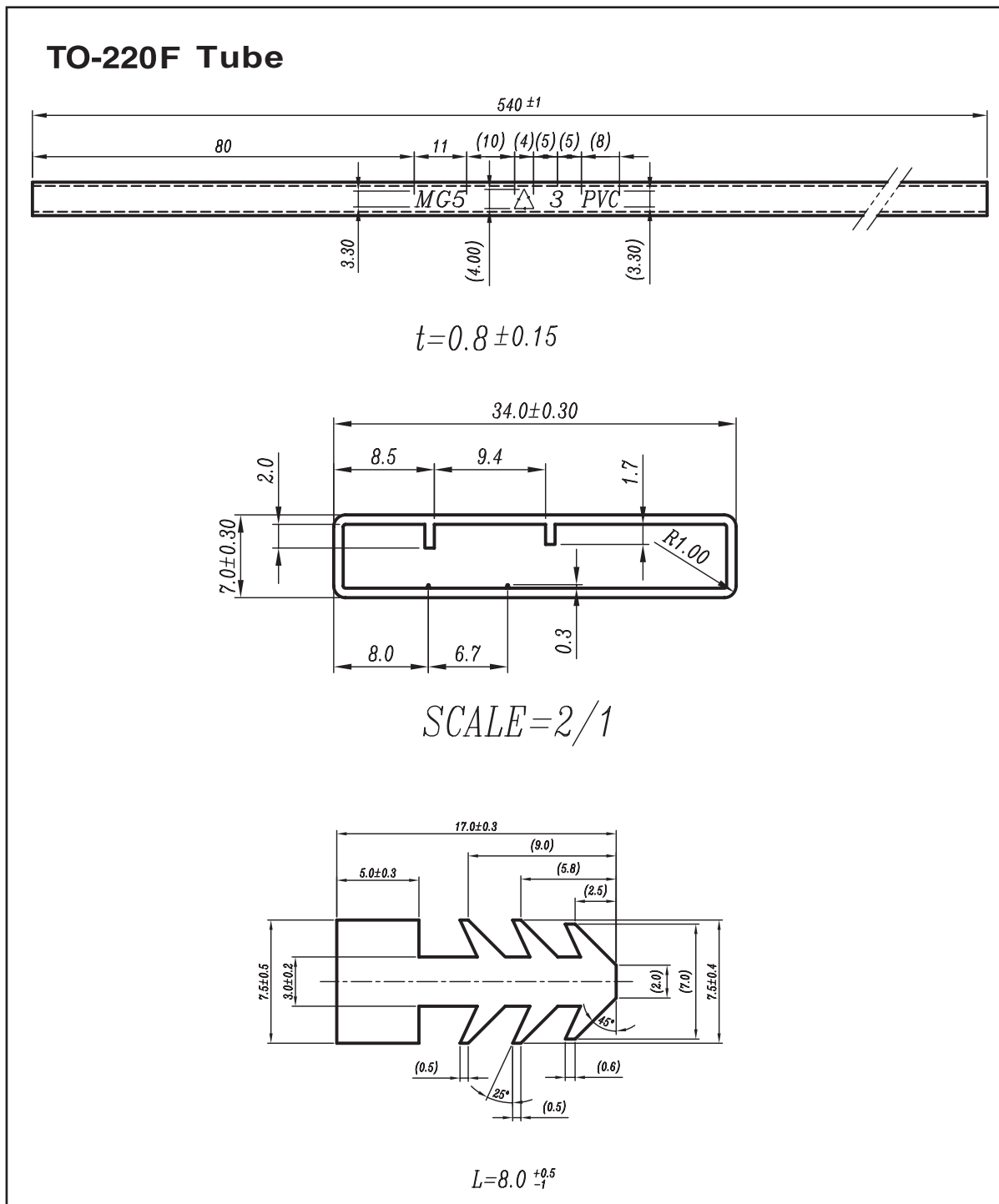


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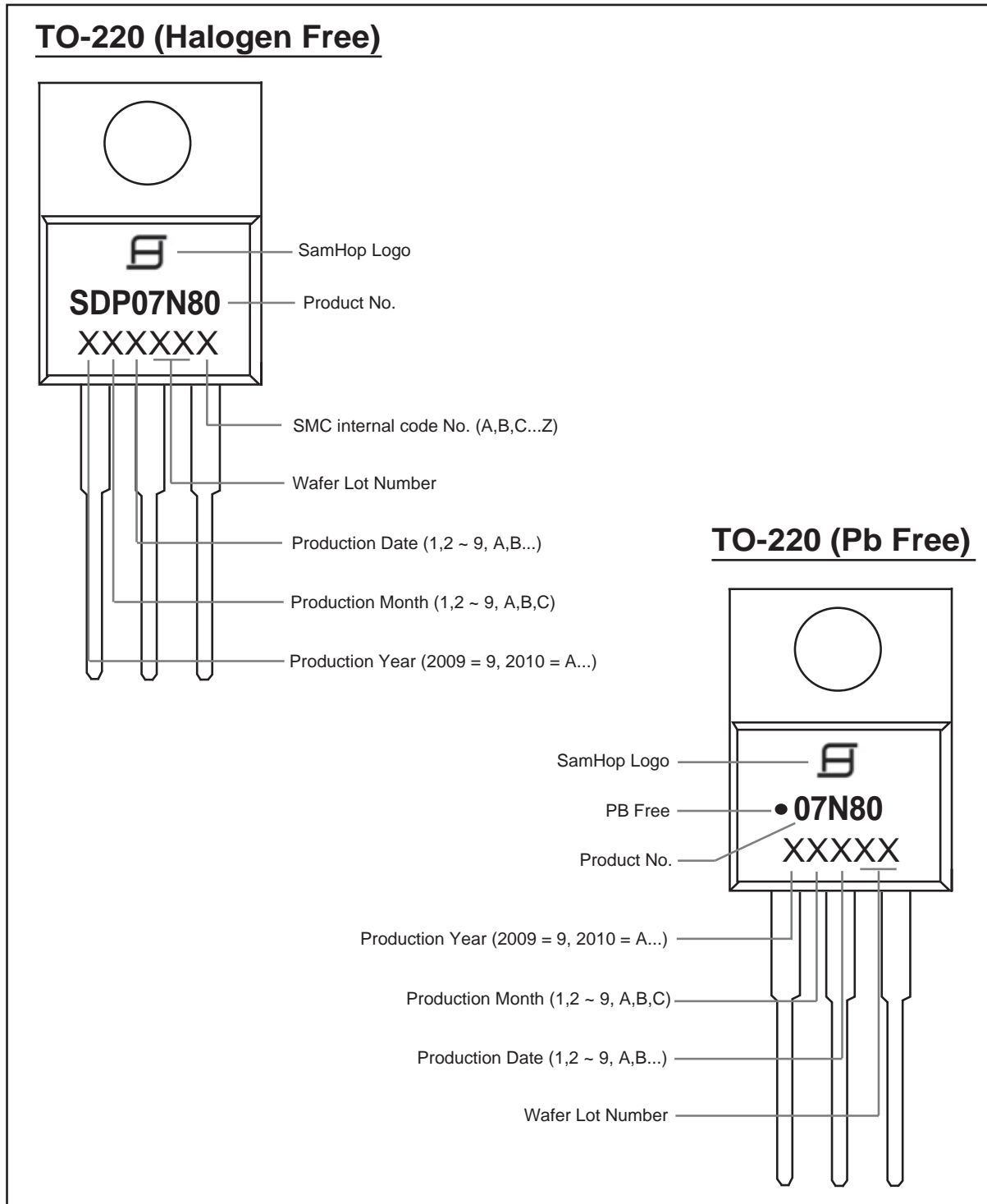
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TOP MARKING DEFINITION



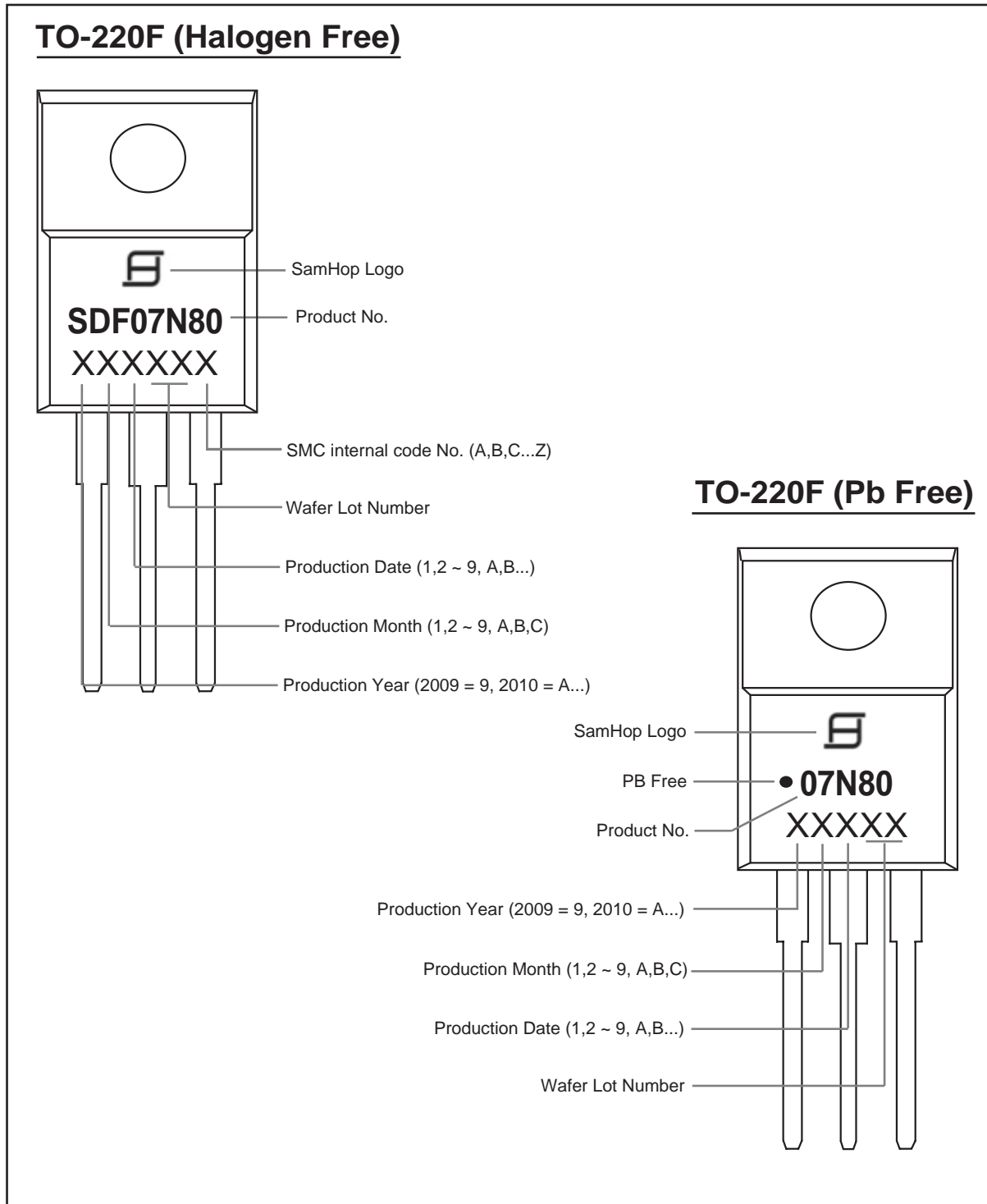
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